

PUBLICATIONS

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- [11] **S. Krishna**, K. Linder, and P. Bhattacharya, “ Photoluminescence linewidth of self-organized $\text{In}_{0.4}\text{Ga}_{0.6}\text{As}/\text{GaAs}$ quantum dots grown on InGaAlAs stressor dots”, *J. Appl. Phys.*, **86**, 4691, 1999.
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